



A Product Line of Diodes Incorporated



FZT491

60V NPN MEDIUM POWER TRANSISTOR IN SOT223

Features

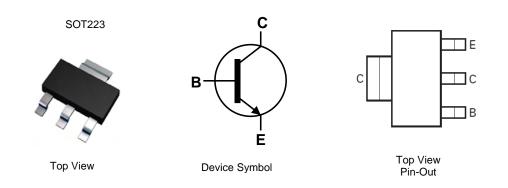
- BV_{CEO} > 60V
- I_C = 1A high Continuous Current
- Low saturation voltage V_{CE(sat)} < 500mV @ 1A
- Complementary PNP Type: FZT591
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Applications

- Power MOSFET gate driving
- Low loss power switching

Mechanical Data

- Case: SOT223
- Case material: molded plastic. "Green" molding compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 ⁽³⁾
- Weight: 0.112 grams (approximate)



Ordering Information (Notes 4)

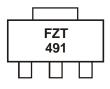
Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT491TA	FZT491	7	12	1,000

Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com

Marking Information



FZT491 = Product Type Marking Code





Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	80	V
Collector-Emitter Voltage	VCEO	60	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	Ι _C	1	А
Peak Pulse Current	I _{CM}	2	A
Base Current	IB	200	mA

Thermal Characteristics

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 5)	Р	2	W	
	(Note 6)	P _D	3	W	
Thermal Resistance, Junction to Ambient	(Note 5)		62.5	°C/W	
	(Note 6)	R _{0JA}	41.7	°C/W	
Thermal Resistance, Junction to Leads (Note 7)		R _{θJL}	19.41	°C/W	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	۵°	

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	≥ 8,000	V	3B
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	С

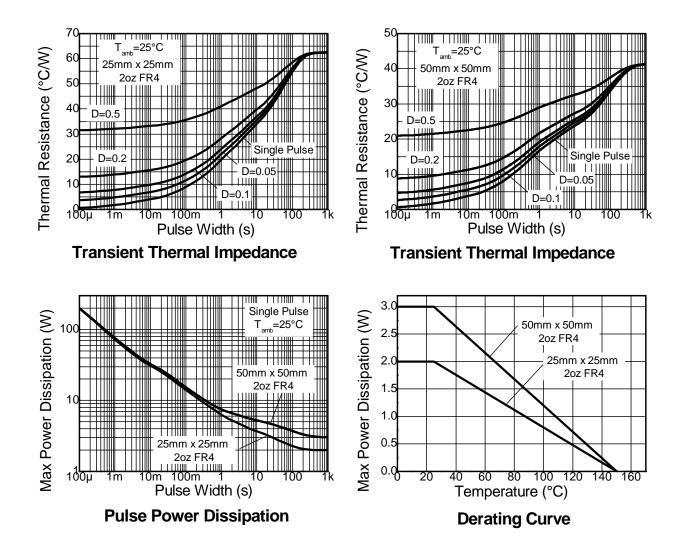
Notes: 5. For a device surface mounted on 25mm X 25mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions; device measured when operating in steady state condition.

Same as note (5), except the device is mounted on 50mm X 50mm single sided 2oz weight copper.
 Thermal resistance from junction to solder-point (at the end of the collector lead).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.





Thermal Characteristics and Derating Information







Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

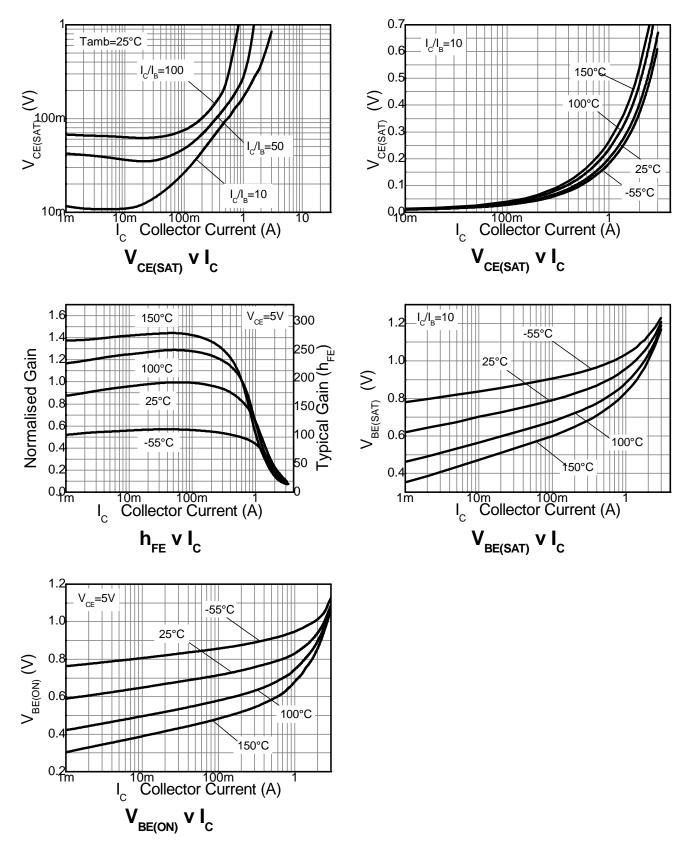
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	80	-	-	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	60	-	-	V	$I_{\rm C} = 10 {\rm mA}$
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.1	-	V	I _E = 100μA
Collector Cut-off Current	I _{CBO}	-	<1	100	nA	$V_{CB} = 60V$
Collector Cut-off Current	ICES	-	<1	100	nA	$V_{CES} = 60V$
Emitter Cut-off Current	I _{EBO}	-	<1	100	nA	V _{EB} = 5.6V
Collector-Emitter Saturation Voltage (Note 9)	V _{CE(sat)}		100 160	250 500	mV	$I_{C} = 500$ mA, $I_{B} = 50$ mA $I_{C} = 1$ A, $I_{B} = 100$ mA
DC Current Gain (Note 9)	h _{FE}	100 100 80 30	140 150 120 40	 300 		$I_{C} = 1mA, V_{CE} = 5V$ $I_{C} = 500mA, V_{CE} = 5V$ $I_{C} = 1A, V_{CE} = 5V$ $I_{C} = 2A, V_{CE} = 5V$
Base-Emitter Turn-On Voltage (Note 9)	V _{BE(on)}	=	830	1000	mV	$I_{C} = 1A, V_{CE} = 5V$
Base-Emitter Saturation Voltage (Note 9)	V _{BE(sat)}	_	965	1100	mV	$I_{\rm C} = 1$ A, $I_{\rm B} = 100$ mA
Output Capacitance	C _{obo}	-	-	10	pF	V _{CB} = 10V, f = 1MHz
Current Gain-Bandwidth Product	f _T	150	-	_	MHz	$V_{CE} = 10V, I_C = 50mA$ f = 100MHz

Notes: 9. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%





Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



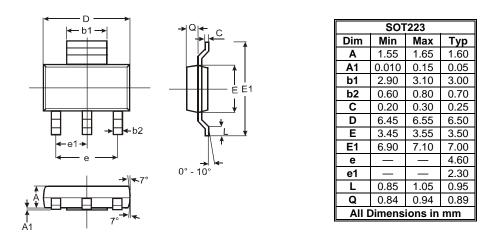
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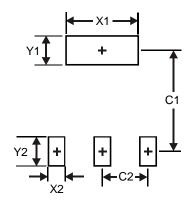
Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
X1	3.3
X2	1.2
Y1	1.6
Y2	1.6
C1	6.4
C2	2.3





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